

TECHNICAL DATA
DATA SHEET 126, REV E**JAN**
JANTX
JANTXV**HIGH CURRENT AXIAL LEAD RECTIFIERS**
DESCRIPTION: 200-1000 VOLT, 3.0 AMP, 2000 NANOSECOND RECTIFIER

-Suffix "US" denotes melf/surface mount packaging

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

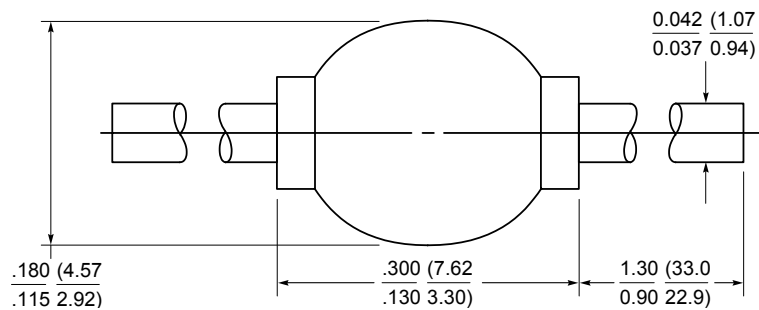
RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) 1N5550 1N5551 1N5552 1N5553 1N5554	-	-	-	200 400 600 800 1000	Vdc
Average DC Output Current (I_o)	$T_A = +55^\circ\text{C}$	-	-	3.0	Amps
Peak Single Cycle Surge Current (I_{fsm})	$t_p = 8.3$ ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Operating and Storage Temp. (T_{op} & T_{stg})	-	-65	-	+175	$^\circ\text{C}$
Maximum Forward Voltage (V_f) 1N5550 1N5551 1N5552 1N5553 1N5554	$I_f = 9.0\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.2 1.2 1.2 1.3 1.3	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	1.0 75	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} = 0.25\text{A}$	-	-	2000	nsec
Thermal Resistance (θ_{JL})	Junction to Lead $d = 0.375''$			22	$^\circ\text{C/W}$
Thermal Resistance (θ_{JEC})	Junction to Endcap	-	-	11	$^\circ\text{C/W}$

SENSITRON **SEMICONDUCTOR**

1N5550/US
1N5551/US
1N5552/US
1N5553/US
1N5554/US

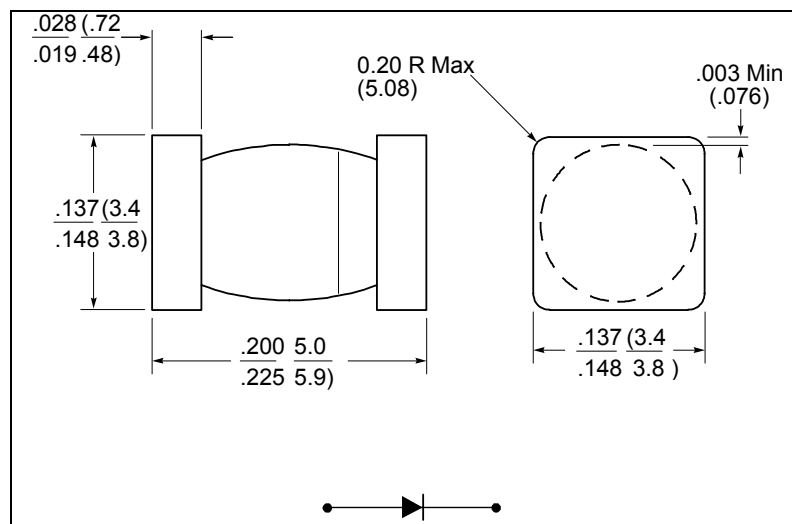
TECHNICAL DATA DATA SHEET 126, REV E

MECHANICAL DIMENSIONS In Inches / (mm), min./max.



PKG. 301

Note: The cathode side is marked with a dark colored band on one side of the diode body.



MELF-B

Note: The cathode side is marked on body with a dark band.

SENSITRON **SEMICONDUCTOR**

1N5550/US
1N5551/US
1N5552/US
1N5553/US
1N5554/US

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